

*Last Search for paper no. 0705*

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	23	("20010004332" "20020000606" "20020142569" "20030194853" "5768192" "6011725" "6030871" "6127227" "6201282" "6215148" "6309927" "6348711" "6538292" "6551880" "6552387" "6566699" "6576511" "6580124" "6596590" "6602805" "6605839" "6642113" "6649971").PN.	US-PGPUB; USPAT	OR	ON	2005/07/14 11:18
S2	2	("5734185" "6248633").pn. jp-2001156188-\$.did.	US-PGPUB; USPAT	OR	ON	2005/07/13 11:08
S3	6	("5734185" "6248633").pn. jp-2001156188-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 11:25
S4	126	(pizarro and (marcos marcus)).xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:45
S5	8908	(hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:45
S6	385	S5 and trapping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:45
S7	247	S6 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:46
S8	246	S6 and source same drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:46
S9	69	S7 and (atomic adj layer adj deposition ald atomic adj layer adj chemical adj vapor adj deposition alcvd al-cvd atomic-layer adj chemival adj vapor adj deposition atomic-layer adj cvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:05

S10	188	(multi adj bit multi-bit 2-bit two-bit two adj bit) and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:39
S11	179	S10 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:05
S12	26	S11 and (atomic adj layer adj deposition ald atomic adj layer adj chemical adj vapor adj deposition alcvd al-cvd atomic-layer adj chemival adj vapor adj deposition atomic-layer adj cvd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:27
S13	2	(increase with trapping adj (site center) with (implantation plasma))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:29
S14	28	trapping adj (site center) with (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:33
S15	1	trapping adj (site center) with (implantation plasma) and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:28
S16	11	("6674138" "6794764" "6804136" "6451641" "20040108537").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:35
S17	9	(multi adj bit multi-bit 2-bit two-bit two adj bit) and (hfo2 "hfo.sub.2" hafnium adj oxide) and angle with implantation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:43

S18	5	(multi adj bit multi-bit 2-bit two-bit two adj bit) and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:46
S19	1	257/324.cor. and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:47
S20	5	257/324 and angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:48
S21	1	"257"/\$3 and advantage with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:49
S22	2	advantage with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:49
S23	45	(increase decrease lower improve inhibit avoid eliminate allow permit) with angle with implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:50
S24	42	trapping with increase with (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:37
S25	1242	trapping adj layer trapping-layer and (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:38

S26	433	(trapping adj layer trapping-layer) and (implantation plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:38
S27	133	(trapping adj layer trapping-layer) and (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:39
S28	39	(trapping adj layer trapping-layer) same (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:51
S29	43	trapping with (implantation plasma) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:53
S30	12	trapping with (site center) with (create generate form) and (multi adj bit multi-bit 2-bit two-bit two adj bit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:56
S31	18	trapping with (site center) with (create generate form) with layer and "257"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:03
S32	14	S31 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:56
S33	5	trapping with (site center) with (induced induce) with layer and "257"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:04

S34	9	trapping with (site center) with (created generated) with layer and "257"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:06
S35	5	plasma with (oxygen nitrogen hydrogen) with trapping with (site center)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:07
S36	56	plasma with (oxygen nitrogen hydrogen) with trapping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S37	0	plasma with (oxygen nitrogen hydrogen) with trapping adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S38	7	plasma with (oxygen nitrogen hydrogen) with trapping with charge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S39	11	(post-anneal post-annealing anneal annealing) with (stoichiometric densify densification) same (hfo2 "hfo. sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:33
S40	52	angle adj implantation with (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:14
S41	171	densification with metal adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:14

S42	1	densification with metal adj oxide with improve	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:15
S43	4	densification with metal adj oxide with mechanical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:16
S44	32	densification with metal adj oxide and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:20
S45	35	densification with (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S46	0	densification with vacant and (hfo2 "hfo.sub.2" hafnium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S47	0	densification with fill with vacant and high-k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S48	0	densification with fill with vacant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:24
S49	0	densification with vacant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25

S50	207	densification with fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25
S51	14	densification with fill with oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 19:25
S52	1217	plasma same nitrogen same exposure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19
S53	3	S52 same charge same trap\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19